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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/902,277	07/09/2001	Gurtej S. Sandhu	MI22-1780	1605
21567 7	7590 01/15/2003			
WELLS ST. JOHN ROBERTS GREGORY & MATKIN P.S. 601 W. FIRST AVENUE SUITE 1300			EXAMINER	
			SCHILLINGER, LAURA M	
SPOKANE, WA 99201-3828			ART UNIT	PAPER NUMBER
•			2813	11/
			DATE MAILED: 01/15/2003	14

Please find below and/or attached an Office communication concerning this application or proceeding.

			j/		
•	Application No.	Applicant(s)	_/		
	09/902,277	SANDHU ET AL.			
. Office Action Summary	Examiner	Art Unit			
	Laura M Schillinger	2813			
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	correspondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period was really received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).			
Status	Octobor 2002				
1) Responsive to communication(s) filed on 22 (	is action is non-final.				
7.2		rosecution as to the merits is			
<ul> <li>Since this application is in condition for allowed closed in accordance with the practice under placed condition.</li> <li>Disposition-of-Claims.</li> </ul>	Ex parte Quayle, 1935 C.D. 11, 4	153 O.G. 213.			
4) $\boxtimes$ Claim(s) <u>51-58</u> is/are pending in the application	n.				
4a) Of the above claim(s) is/are withdraw	wn from consideration.				
5)⊠ Claim(s) <u>58</u> is/are allowed.					
6)⊠ Claim(s) <u>51-57</u> is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/o	r election requirement.				
Application Papers					
9) The specification is objected to by the Examine					
10)☐ The drawing(s) filed on is/are: a)☐ accept					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
11) The proposed drawing correction filed on		oved by the Examiner.			
If approved, corrected drawings are required in rep	•				
12) The oath or declaration is objected to by the Ex	annier.				
Priority under 35 U.S.C. §§ 119 and 120		-) (d) == (f)			
13) Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C. § 119(8	a)-(a) or (t).			
a) All b) Some * c) None of:	La contra de la contra del la contra de la contra de la contra del la contra de la contra de la contra de la contra del la contra de la contra de la contra del la contra de la contra de la contra del la contra de				
1. Certified copies of the priority document		ian Na			
2. Certified copies of the priority document					
<ul> <li>3. Copies of the certified copies of the prior</li> <li>application from the International But</li> <li>* See the attached detailed Office action for a list</li> </ul>	reau (PCT Rule 17.2(a)).				
14) ☐ Acknowledgment is made of a claim for domesti	ic priority under 35 U.S.C. § 119(	e) (to a provisional application	1).		
a) ☐ The translation of the foreign language pro 15)☐ Acknowledgment is made of a claim for domest					
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal	y (PTO-413) Paper No(s) Patent Application (PTO-152)			
LLS Patent and Tradamark Office					

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#### **DETAILED ACTION**

This Office Action is in Response to Amendment F dated 10/22/02, in Paper No.13.

### **EXAMINER'S AMENDMENT**

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Jennifer Taylor on 1/10/03.

The application has been amended as follows:

Cancel claims 37-38 and 43-50.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

<sup>(</sup>e) the invention was described in-

<sup>(1)</sup> an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or

<sup>(2)</sup> a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).

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Claims 51-57 are rejected under 35 U.S.C. 102(e) as being anticipated by Tseng et al ('802).

In reference to claim 51, Tseng et al ('802) teaches a method comprising:

Forming a gate (Col.2, lines: 45-55)

Forming a polycrystalline TFT layer over the gate (Col.2, lines: 45-55)

Forming a fluorine containing layer proximate to the polycrystalline TFT layer, the fluorine layer comprising W (Col.2, lines: 45-55) and

Transferring F into the polycrystalline TFT layer from the F containing layer (Col.2-3, lines: 60-5).

In reference to claim 52, Tseng et al ('802) teaches wherein the polycrystalline TFT comprises Si (Col.2, lines: 50-55)

In reference to claim 53, Tseng et al ('802) teaches wherein the forming a F containing layer comprises forming a sacrificial F containing layer over the TFT layer by CVD utilizing WF(6) and SiH(4) precursors (Col.2, lines: 55-60).

In reference to claim 54, Tseng et al ('802) teaches further comprising after the transferring F, removing the F-containing layer from over the TFT layer (Col.3, lines: 60-63)).

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In reference to claim 55, Tseng et al ('802) teaches a method comprising:

Forming a gate (Col.2, lines: 45-55)

Forming a polycrystalline TFT layer over the gate (Col.2, lines: 45-55)

Forming a fluorine containing layer proximate to the polycrystalline TFT layer, the fluorine layer comprising W (Col.2, lines: 45-55);

Providing a buffering layer intermediate the TFT layer and the F containing layer (Col.3, lines: 15-25); and

Transferring F into the polycrystalline TFT layer from the F containing layer (Col.2-3, lines: 60-5).

In reference to claim 56, Tseng et al ('802) wherein the F-containing layer comprises W (Col.2, lines: 45-55).

In reference to claim 57, Tseng et al ('802) wherein the buffering layer comprises SiO<sub>2</sub> (Col.3, lines: 15-25).

## Allowable Subject Matter

The following is a statement of reasons for the indication of allowable subject matter:

Claim 58 recites wherein the polycrystalline thin film layer is germanium. Although Germanium polycrystalline layers are well-known in the art of semiconductor technology, Tseng makes no suggestion to modify his teachings to include forming a germanium polycrystalline

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silicon layer rather than a polycrystalline silicon layer. Absent such a suggestion or teaching,

claim 58 contains allowable subject matter.

Response to Arguments

Applicant's arguments filed 10/22/02 have been fully considered but they are not

persuasive. Applicant argues that claims 51-58 are allowable over prior art Nishimura-however

claims 51-58 are newly pending and were not rejected by the Examiner based on Nishimura.

(See Interview Summary) Consequently, Applicant's arguments are considered moot.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Laura M Schillinger whose telephone number is (703) 308-6425.

The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Carl W Whitehead, Jr. can be reached on (703) 308-4940. The fax phone numbers

for the organization where this application or proceeding is assigned are (703) 308-7722 for

regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-1500.

CARL WHITEHEAD, JR. SUPERVISORY PATENT EXACTOR

TECHNOLOGY CENTER 2800

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LMS

January 10, 2003

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